Vishay Semiconductors

RoHS

COMPLIANT

HALOGEN FREE

Thyristor, Surface Mount, Phase Control SCR, 16 A



PRIMARY CHARACTERISTICS						
I _{T(AV)}	16 A					
V_{DRM}/V_{RRM}	800 V, 1200 V					
V_{TM}	1.25 V					
I _{GT}	45 mA					
T_J	-40 to +125 °C					
Package	D ² PAK (TO-263AB)					
Circuit configuration	Single SCR					

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- · Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-25TTS...S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5							
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A						
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	16.5	25.0							

Note

• $T_A = 55$ °C, $T_J = 125$ °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I _{T(AV)}	Sinusoidal waveform	16	۸					
I _{RMS}		25	А					
V _{RRM} /V _{DRM}		800 to 1200	V					
I _{TSM}		350	A					
V _T	16 A, T _J = 25 °C	1.25	V					
dV/dt		500	V/µs					
dl/dt		150	A/µs					
TJ		-40 to +125	°C					

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} , AT 125 °C mA
VS-25TTS08S-M3	800	800	10
VS-25TTS12S-M3	1200	1200]



Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEC	T CONDITIONS	VAL	UNITS				
PARAMETER	STINIBUL	STMBOL TEST CONDITIONS				UNITS			
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	onduction half sine wave	16					
Maximum RMS on-state current	I _{RMS}			2	5	Α			
Maximum peak, one-cycle,	I	10 ms sine pulse, r	ated V _{RRM} applied	30	00	_ A			
non-repetitive surge current	I _{TSM}	10 ms sine pulse, r	no voltage reapplied	35	50				
Maximum I ² t for fusing	I ² t	10 ms sine pulse, rated V _{RRM} applied		45	50	A ² s			
Maximum 1-t for fusing	1-1	10 ms sine pulse, r	no voltage reapplied	630		A-S			
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to 10 ms	t = 0.1 ms to 10 ms, no voltage reapplied			A²√s			
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C		1.25		V			
On-state slope resistance	r _t	T _{.1} = 125 °C		12	2.0	mΩ			
Threshold voltage	$V_{T(TO)} = 123 \text{ G}$.0	V				
Maximum reverse and direct leakage current	1/1	T _J = 25 °C	V _B = rated V _{BBM} /V _{DBM}	0.	.5				
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	VR = rated VRRM/VDRM	1	0				
Holding current	I _H	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial $I_T = 1$ A, $T_J = 25$ °C	-	150	mA			
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C			Anode supply = 6 V, resistive load, T _J = 25 °C		20	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = open$			00	V/µs			
Maximum rate of rise of turned-on current	dl/dt				150				

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P_{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	VV	
Maximum peak positive gate current	+ I _{GM}		1.5	Α	
Maximum peak negative gate voltage	- V _{GM}		10	V	
		Anode supply = 6 V, resistive load, T _J = - 10 °C	60	mA	
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, $T_J = 25$ °C	45		
		Anode supply = 6 V, resistive load, T_J = 125 °C	20		
		Anode supply = 6 V, resistive load, T _J = - 10 °C	2.5		
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0 V		
		Anode supply = 6 V, resistive load, $T_J = 125 ^{\circ}\text{C}$	1.0	V	
Maximum DC gate voltage not to trigger	V_{GD}	T = 105 °C V = reted value	0.25		
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = rated value	2.0	mA	

SWITCHING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9						
Typical reverse recovery time	t _{rr}	T 105 °C	4	μs					
Typical turn-off time	t _q	T _J = 125 °C	110						

Vishay Semiconductors

THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER	VALUES	UNITS							
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C					
Maximum thermal resistance, junction to case	R _{thJC}	R _{thJC} DC operation		°C/W					
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	C/VV					
Approximate weight			2	g					
Approximate weight			0.07	OZ.					
Marking device		Case style D ² PAK (TO-263AB)	25TTS08S						
ivial killy device		Case style D-FAR (10-203AB)	25TTS12S						

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

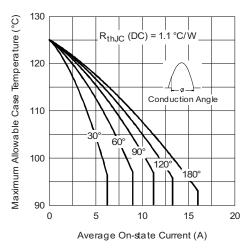


Fig. 1 - Current Rating Characteristics

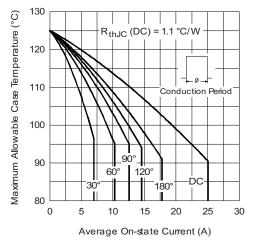


Fig. 2 - Current Rating Characteristics

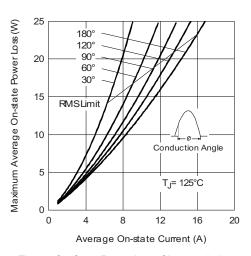


Fig. 3 - On-State Power Loss Characteristics

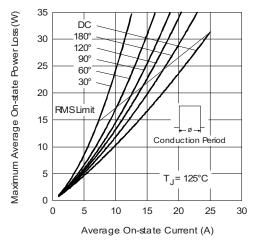


Fig. 4 - On-State Power Loss Characteristics

www.vishay.com

Vishay Semiconductors

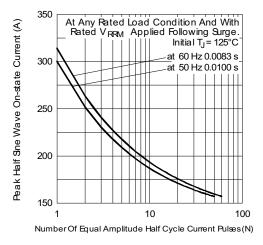


Fig. 5 - Maximum Non-Repetitive Surge Current

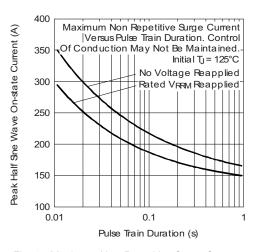


Fig. 6 - Maximum Non-Repetitive Surge Current

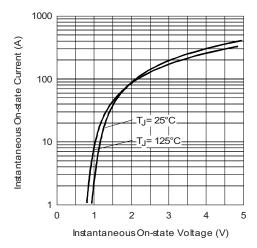


Fig. 7 - On-State Voltage Drop Characteristics

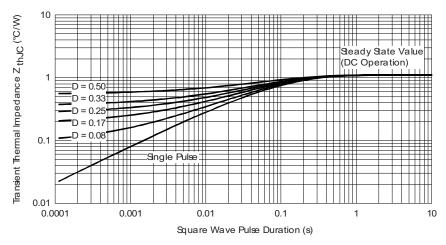


Fig. 8 - Gate Characteristics

Vishay Semiconductors

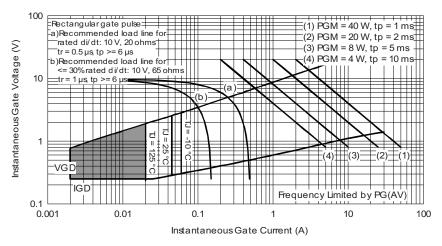
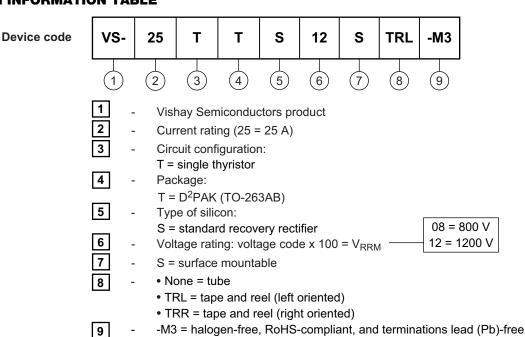


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-25TTS08S-M3	50	1000	Antistatic plastic tubes						
VS-25TTS08STRR-M3	800	800	13" diameter reel						
VS-25TTS08STRL-M3	800	800	13" diameter reel						
VS-25TTS12S-M3	50	1000	Antistatic plastic tubes						
VS-25TTS12STRR-M3	800	800	13" diameter reel						
VS-25TTS12STRL-M3	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?96164</u>					
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				



Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	NOTES	STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.